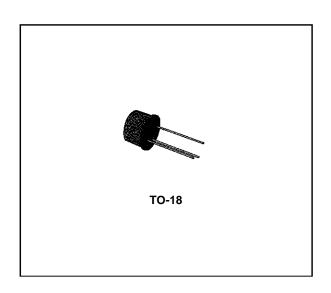
BC177 BC178-BC179

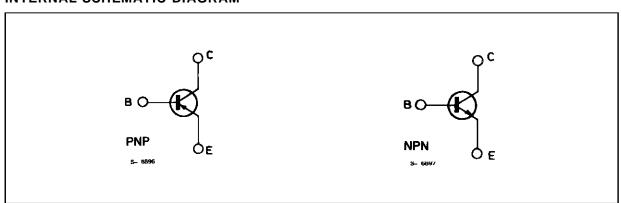
LOW NOISE GENERAL PURPOSE AUDIO AMPLIFIERS

DESCRIPTION

The BC177, BC178 and BC179 are silicon planar epitaxial PNP transistors in TO-18 metal case. They are suitable for use in driver audio stages, low noise input audio stages and as low power, high gain general purpose transistors. The complementary NPN types are respectively the BC107, BC108 and BC109.



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		I I m i 4		
Symbol	Parameter	BC177	BC178	BC179	Unit
V_{CES}	Collector-emitter Voltage (V _{BE} = 0)	- 50	- 30	- 25	V
V_{CEO}	Collector-emitter Voltage (I _B = 0)	- 45	- 25	- 20	V
V _{EBO}	Emitter-base Voltage (I _C = 0)	- 5		V	
Ic	Collector Current	- 100		mA	
I _{CM}	Collector Peak Current	- 200		mA	
P _{tot}	Total Power Dissipation at T _{amb} ≤ 25 °C	300		mW	
T _{stg}	Storage Temperature	- 65 to 175		°C	
Tj	Junction Temperature	175		°C	

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THERMAL DATA

R _{th j-case}	Thermal Resistance Junction-case	Max	200	°C/W
R _{th j-amb}	Thermal Resistance Junction-ambient	Max	500	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C unless otherwise specified)

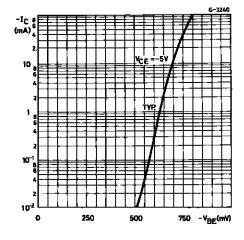
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cutoff Current (V _{BE} = 0)	V _{CE} = -20 V V _{CE} = -20 V T _{amb} = 150 °C		- 1	- 100 - 10	nA μA
V _{(BR)CEO} *	Collector-emitter Breakdown Voltage (I _B = 0)	I _C = -2 mA for BC177 for BC178 for BC179	- 45 - 25 - 20			> > >
V _(BR) CES	Collector-emitter Breakdown Voltage (V _{BE} = 0)	I _C = - 10 μA for BC177 for BC178 for BC179	- 50 - 30 - 25			V V V
V _{(BR)EBO}	Emitter-base Breakdown Voltage (I _C = 0)	I _E = - 10 μA	- 5			V
V _{CE(sat)} *	Collector-emitter Saturation Voltage	$I_C = -10 \text{ mA}$ $I_B = -0.5 \text{ mA}$ $I_C = -100 \text{ mA}$ $I_B = -5 \text{ mA}$		- 75 - 200	- 250	mV mV
V _{BE} *	Base-emitter Voltage	$I_C = -2 \text{ mA}$ $V_{CE} = -5 \text{ V}$	- 550	- 640	- 750	mV
$V_{BE(sat)}$	Base-emitter Saturation Voltage	$I_C = -10 \text{ mA}$ $I_B = -0.5 \text{ mA}$ $I_C = -100 \text{ mA}$ $I_B = -5 \text{ mA}$		- 720 - 860		mV mV
h _{fe}	Small Signal Current Gain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	125 240 125 240 240		260 500 260 500 500	

^{*} Pulsed: pulsed duration = 300 μs, duty cycle = 1 %.

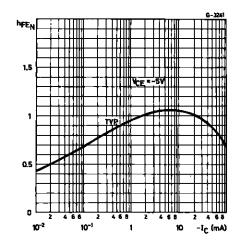
ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test (Conditions	Min.	Тур.	Max.	Unit
f _T	Transition Frequency	$I_C = -10 \text{ mA}$ f = 100 MHz	$V_{CE} = -5 V$		200		MHz
ССВО	Collector-base Capacitance	I _E = 0	$V_{CB} = -10 \text{ V}$		5.0		pF
NF	Noise Figure	$I_C = -0.2 \text{ mA}$ $R_g = 2 \text{ k}\Omega$ $B = 200 \text{ Hz}$	$V_{CE} = -5 V$ f = 1 kHz				
			for BC177 for BC178 for BC179		2 2 1.2	10 10 4	dB dB dB
h _{ie}	Input Impedance	$I_C = -2 \text{ mA}$ f = 1 kHz	$V_{CE} = -5 V$				
			for BC177 Gr. A		2.7		kΩ
			for BC177 Gr. B		5.2		kΩ
			for BC178 Gr. A for BC178 Gr. B		2.7 5.2		kΩ kΩ
			for BC179 Gr. B		5.2		kΩ
h _{re}	Reverse Voltage Ratio	$I_C = -2 \text{ mA}$ f = 1 kHz	V _{CE} = -5 V				
			for BC177 Gr. A		2.7x10 ⁻⁴		
			for BC177 Gr. B for BC178 Gr. A		4.5x10 ⁻⁴ 2.7x10 ⁻⁴		
			for BC178 Gr. B		4.5x10 ⁻⁴		
			for BC179 Gr. B		4.5x10 ⁻⁴		
h _{oe}	Output Admittance	$I_C = -2 \text{ mA}$ f = 1 kHz	V _{CE} = -5 V				
			for BC177 Gr. A		25		μS
			for BC177 Gr. B		35		μS
			for BC178 Gr. A for BC178 Gr. B		25 35		μS μS
			for BC179 Gr. B		35		μS μS

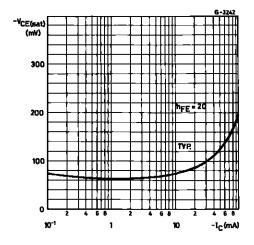
DC Transconductance.



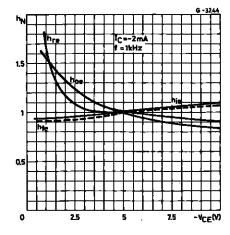
DC Normalized Current Gain.



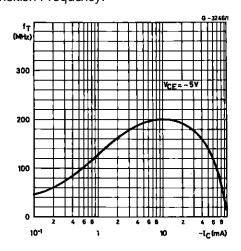
Collector-emitter Saturation Voltage.



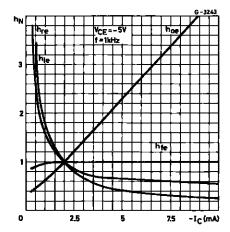
Normalized h Parameters.



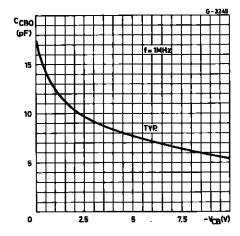
Transition Frequency.



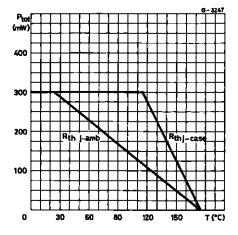
Normalized h Parameters.



Collector-base Capacitance.

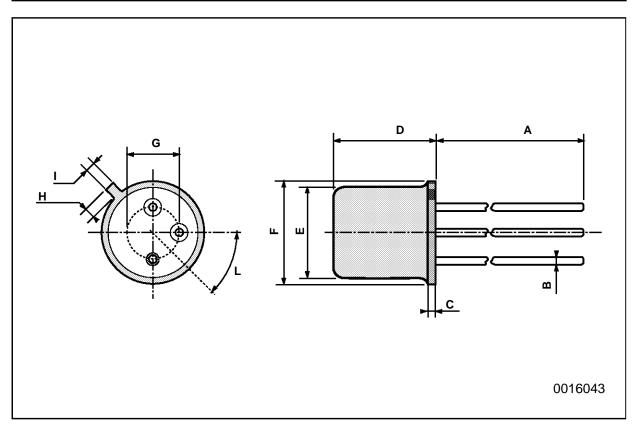


Power Rating Chart.



TO-18 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А		12.7			0.500		
В			0.49			0.019	
D			5.3			0.208	
Е			4.9			0.193	
F			5.8			0.228	
G	2.54			0.100			
Н			1.2			0.047	
I			1.16			0.045	
L	45°			45°			



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